



SDI FINAL EVALUATION FORM 1.1

PART 1:

Journal Name:	Physical Science International Journal
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

PART 2:

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
The authors improved the paper but the presented version requires a complementary work, particularly, at the level of the paragraph 3. The authors analyzed in the paragraph 2 the transistors breakdown phenomenon, but in the paragraph 3, the author does not take it into account . This point must be analyzed in the final version.	The breakdown due to impact ionization in the form of non punch-through analysis is address in this version. . Two equations are also added to clarify the mechanism for modeling breakdown voltage. Please see lines 155-175